## WHAT IS CLAIMED IS:

1. A composition, comprising a siloxane resin having the formula: (HSiO<sub>3/2</sub>)<sub>a</sub>(SiO<sub>4/2</sub>)<sub>b</sub>(HSiX<sub>3/2</sub>)<sub>c</sub>(SiX<sub>4/2</sub>)<sub>d</sub>,

wherein each X is independently -O-, -OH, or -O-( $CH_2$ )<sub>m</sub>-Z<sub>n</sub>, provided at least one X is -O-( $CH_2$ )<sub>m</sub>-Z<sub>n</sub>, wherein Z<sub>n</sub> is a polycyclic aromatic hydrocarbon moiety comprising n aromatic rings, wherein each m is independently an integer from 1 to about 5, Z is an aromatic moiety, and each n is independently an integer from 1 to about 6;

$$0 < a < 1, 0 < b < 1, 0 < c < 1, 0 < d < 1, and  $a + b + c + d = 1$ .$$

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- 2. The composition of claim 1, wherein  $0.3 \le a \le 0.7$ ,  $0.3 \le b \le 0.7$ , and  $0 < (c + d) \le 0.6$ .
- 3. The composition of claim 1, wherein each X is independently -O-, -OH, or -O-(CH<sub>2</sub>)-Z<sub>3</sub>, provided at least one X is -O-(CH<sub>2</sub>)<sub>m</sub>-Z<sub>3</sub>.
  - 4. The composition of claim 3, wherein  $-(CH_2)_m$ - $Z_3$  is a 9-anthracene methylene moiety.
  - 5. The composition of claim 1, further comprising an organic solvent.

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- 6. The composition of claim 5, wherein the organic solvent is 2-ethoxyethanol, 1-methoxy-2-propanol, or propylene glycol monoether.
- 7. A method for preparing a dyed siloxane resin composition, comprising:

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- (i) reacting a trialkoxysilane, a tetraalkoxysilane, and water, in the presence of a hydrolysis catalyst, to form a first siloxane resin having HSiO<sub>3/2</sub>, SiO<sub>4/2</sub>, HSiX'<sub>3/2</sub>, and SiX'<sub>4/2</sub> units, wherein X' is independently -O- or -OH, and having substantially no silicon-carbon bonds; and
- (ii) reacting the first siloxane resin with a compound having the formula HO (CH<sub>2</sub>)<sub>m</sub>-Z<sub>n</sub>, wherein each m is independently an integer from 1 to about 5, Z is an aromatic moiety, and each n is independently an integer from 1 to about 6, to form the dyed siloxane resin composition.
  - 8. The method of claim 7, wherein the hydrolysis catalyst is a base or an acid.

WO 2004/113417 PCT/US2004/016265

- 9. The method of claim 8, wherein the hydrolysis catalyst is a mineral acid.
- 10. The method of claim 7, wherein reacting step (ii) is performed at a temperature from about 25°C to about the boiling temperature of a reaction component and for a duration of about 10 min to about 60 min.
  - 11. The method of claim 7, wherein reacting step (ii) is performed in the presence of a mineral acid.
  - 12. The method of claim 7, wherein reacting steps (i) and (ii) are performed simultaneously.

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13. A dyed siloxane resin composition, prepared by the method of claim 7.

about 6; 0 < a < 1, 0 < b < 1, 0 < c < 1, 0 < d < 1, and a + b + c + d = 1; and

- 14. A method of preparing an anti-reflective coating on a substrate, comprising:
- (i) coating a composition onto a substrate to form a coated substrate, wherein the composition comprises a siloxane resin having the formula  $(HSiO_{3/2})_a (SiO_{4/2})_b (HSiX_{3/2})_c (SiX_{4/2})_d, \text{ wherein each } X \text{ is independently -O-, -OH, or -O-} (CH_2)_m-Z_n, \text{ provided at least one } X \text{ is -O-}(CH_2)_m-Z_n, \text{ wherein } Z_n \text{ is a polycyclic aromatic hydrocarbon moiety comprising n aromatic rings, wherein each m is independently an integer from 1 to about 5, Z is an aromatic moiety, and each n is independently an integer from 1 to$ 
  - (ii) curing the coated substrate, to form the anti-reflective coating on the substrate.
- 15. The method of claim 14, wherein the curing step (ii) comprises heating the coated substrate at about 50°C to about 300°C for a duration of about 0.1 min to about 60 min.
- 16. The method of claim 15, wherein the curing step (ii) comprises heating the coated substrate at about 150°C to about 275°C for a duration of about 1 min to about 5 min.
  - 17. The method of claim 15, wherein the curing step (ii) is performed under an inert atmosphere.

WO 2004/113417 PCT/US2004/016265

18. The method of claim 17, wherein the inert atmosphere consists essentially of nitrogen.

19. A semiconductor wafer, prepared according to the method of claim 14.